

SiC Power MOSFET Module

1200 V, 80 mΩ, 31 A
Full Bridge Power Module

NVXK2PR80WXT2

Features

- DIP Silicon Carbide Full Bridge Power Module for On-Board Charger (OBC) for xEV Applications
- Creepage and Clearance per IEC60664-1, IEC 60950-1
- Compact Design for Low Total Module Resistance
- Module Serialization for Full Traceability
- Lead Free, ROHS and UL94V-0 Compliant
- Automotive Qualified per AEC-Q101 and AQG324

Typical Applications

- DC-DC and On-Board Charger in xEV Applications

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	1200	V
Gate-to-Source Voltage	V _{GS}	+25/-15	V
Recommended Operation Values of Gate-to-Source Voltage, T _J ≤ 175°C	V _{GSop}	+20/-5	V
Continuous Drain Current (Note 1)	I _D	31	A
Power Dissipation (Note 1)	P _D	208	W
Pulsed Drain Current (Note 2)	I _{DM}	153	A
Single Pulse Surge Drain Current Capability	I _{DSC}	425	A
Operating Junction Temperature	T _J	-55 to 175	°C
Storage Temperature	T _{stg}	-40 to 125	°C
Source Current (Body Diode)	I _S	18	A
Single Pulse Drain-to-Source Avalanche Energy (Note 3)	E _{AS}	180	mJ

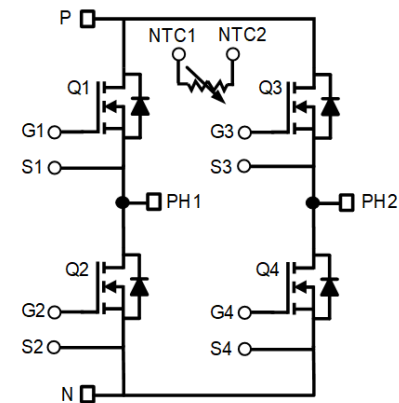
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Note 1)

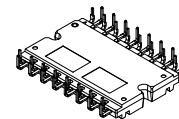
Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-to-Case (Note 1)	R _{θJC}	0.56	0.72	°C/W
Thermal Resistance Junction-to-Sink (Note 1)	R _{ψJS}	0.98	1.14	°C/W

1. Particular conditions specified determine thermal resistance values shown. Infinite heatsink with T_C = 100°C for R_{θJC}. For R_{ψJS} assembled to 3 mm thick aluminum heatsink with infinite cooling bottom surface at 85°C, through 38 μm thick TIM with 6.5 W/mK thermal conductivity.
2. Repetitive rating limited by maximum junction temperature and transconductance.
3. E_{AS} based on initial T_J = 25°C, L = 1 mH, I_{AS} = 19 A, V_{DD} = 120 V, V_{GS} = 18 V.

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max
1200 V	116 mΩ @ 20 V	31 A



SiC MOSFET Full Bridge Module

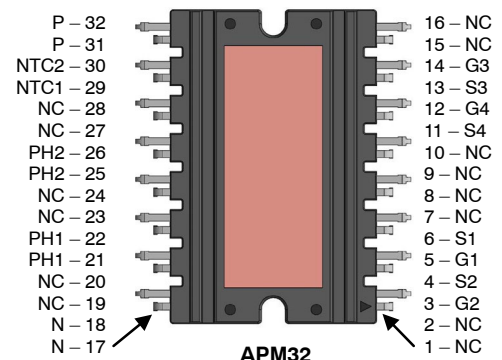


APM32
44.00x28.80x5.70
CASE MODHM

MARKING DIAGRAM

NVXK2PR80WXT2
ZZZ ATYWW
NNNNNNN

NVXK2PR80WXT2 = Specific Device Code
ZZZ = Lot Number
AT = Assembly Site & Test Location
Y = Year
W = Work Week
NNN = Serial Number



ORDERING INFORMATION

Device	Package	Shipping
NVXK2PR80WXT2	APM32	10 ea / Tube

NVXK2PR80WXT2

PIN DESCRIPTION

Pin No.	Pin Name	Description
1, 2, 7, 8, 9, 10, 15, 16, 19, 20, 23, 24, 27, 28	NC	Not Connected pin
3	G2	Q2 Gate
4	S2	Q2 Source
5	G1	Q1 Gate
6	S1	Q1 Source
11	S4	Q4 Source
12	G4	Q4 Gate
13	S3	Q3 Source
14	G3	Q3 Gate
17, 18	B-	Negative Power Terminal
21, 22	PH1	Phase 1 Output
25, 26	PH2	Phase 2 Output
29	NTC1	NTC pin1
30	NTC2	NTC pin2
31, 32	B+	Positive Power Terminal

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	1200	–	–	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} / T _J	I _D = 1 mA, referenced to 25°C	–	500	–	mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, T _J = 25°C	–	–	100	μA
		V _{DS} = 1200 V, T _J = 175°C	–	–	1	mA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = +25/-15 V, V _{DS} = 0 V	–	–	±1	μA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 5 mA	1.8	3	4.3	V
Recommended Gate Voltage	V _{GOP}		–5	–	+20	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 20 V, I _D = 20 A, T _J = 25°C	–	80	116	mΩ
		V _{GS} = 20 V, I _D = 20 A, T _J = 175°C	–	150	–	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 20 V, I _D = 20 A	–	11	–	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 800 V	–	1154	–	pF
Output Capacitance	C _{OSS}		–	79	–	
Reverse Transfer Capacitance	C _{RSS}		–	7.9	–	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = –5/20 V, V _{DS} = 600 V, I _D = 20 A	–	56	–	nC
Threshold Gate Charge	Q _{G(TH)}		–	10	–	
Gate-to-Source Charge	Q _{GS}		–	18	–	
Gate-to-Drain Charge	Q _{GD}		–	11	–	
Gate-Resistance	R _G	V _{GS} = 0 V, f = 1 MHz	–	1.2	–	Ω

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
INDUCTIVE SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5 / 20 \text{ V}$, $V_{DS} = 800 \text{ V}$, $I_D = 20 \text{ A}$, $R_G = 4.7 \Omega$, Inductive load	–	12	–	ns
Rise Time	t_r		–	12	–	
Turn-Off Delay Time	$t_{d(OFF)}$		–	21	–	
Fall Time	t_f		–	9	–	
Turn-On Switching Loss	E_{ON}		–	135	–	μJ
Turn-Off Switching Loss	E_{OFF}		–	46	–	μJ
Total Switching Loss	E_{tot}		–	181	–	μJ

DRAIN-SOURCE DIODE CHARACTERISTICS

Continuous Drain-Source Diode Forward Current (Notes 1)	I_{SD}	$V_{GS} = -5 \text{ V}$, $T_J = 25^\circ\text{C}$	–	–	31	A
Pulsed Drain-Source Diode Forward Current (Note 2)	I_{SDM}	$V_{GS} = -5 \text{ V}$, $T_J = 25^\circ\text{C}$	–	–	153	A
Forward Diode Voltage	V_{SD}	$V_{GS} = -5 \text{ V}$, $I_{SD} = 10 \text{ A}$, $T_J = 25^\circ\text{C}$	–	3.9	–	V
Reverse Recovery Time	t_{RR}	$V_{GS} = -5 \text{ V}$, $dI_S/dt = 1000 \text{ A}/\mu\text{s}$, $I_{SD} = 20 \text{ A}$	–	16.2	–	ns
Peak Reverse Recovery Current	I_{RRM}		–	7.6	–	A
Reverse Recovery Energy	E_{REC}		–	4.1	–	μJ
Reverse Recovery Charge	Q_{RR}		–	61.6	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse test: pulse width $\leq 300 \mu\text{s}$, duty ratio $\leq 2\%$.

COMPONENTS

Component	Description	Type	Quantity	Specification
NTC	10 k Ω , $\pm 3\%$ Case Size 0603	Discrete	1	B Constants $B_{25/50} = 3590$ $B_{25/85} = 3635$ $B_{25/100} = 3650 \pm 3\%$

TYPICAL CHARACTERISTICS SIC MOSFET

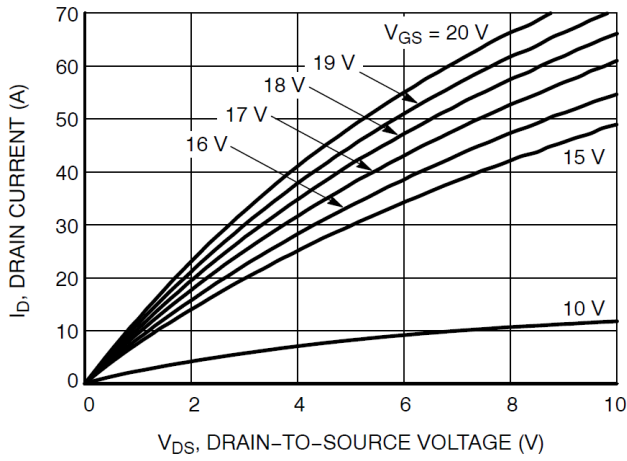


Figure 1. On-Region Characteristics

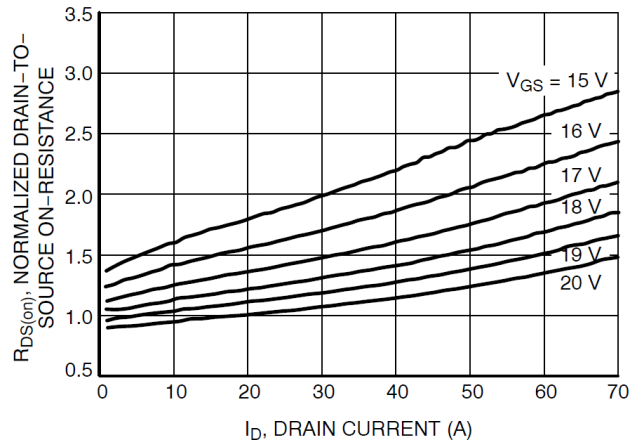


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

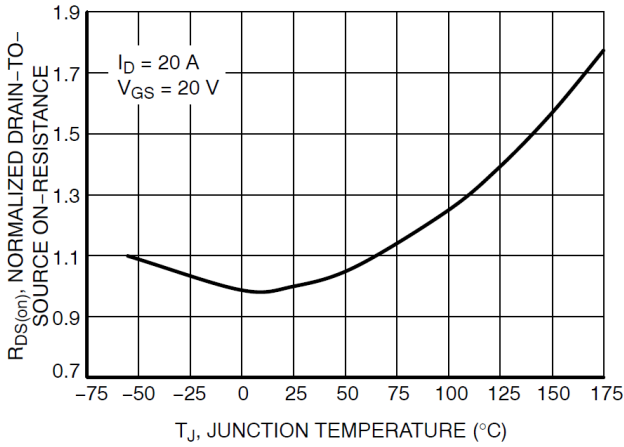


Figure 3. On-Resistance Variation with Temperature

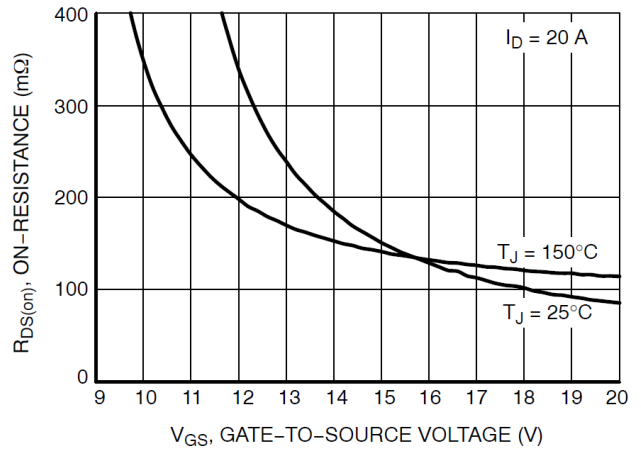


Figure 4. On-Resistance vs. Gate-to-Source Voltage

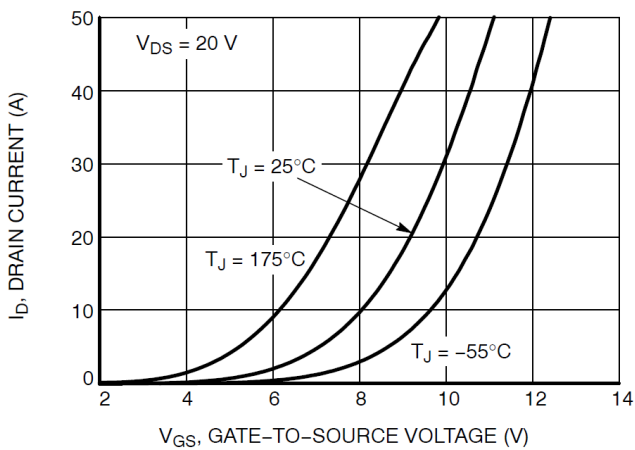


Figure 5. Transfer Characteristics

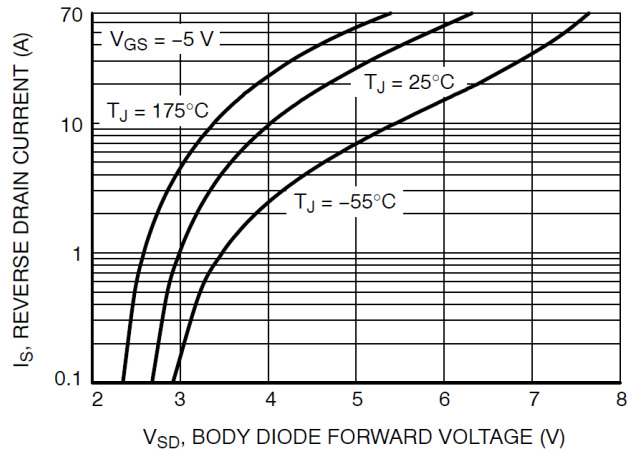


Figure 6. Diode Forward Voltage vs. Current

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TYPICAL CHARACTERISTICS SIC MOSFET (continued)

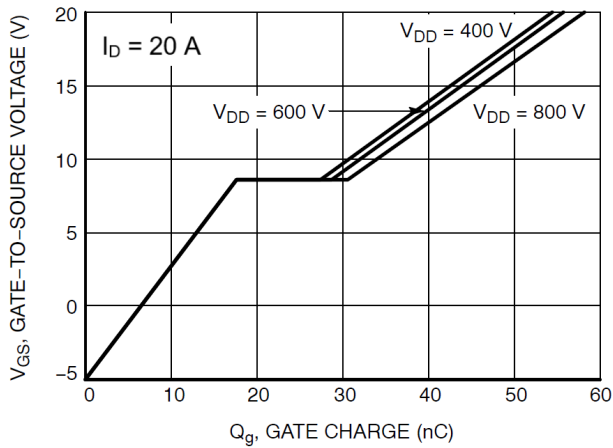


Figure 7. Gate-to-Source Voltage vs. Total Charge

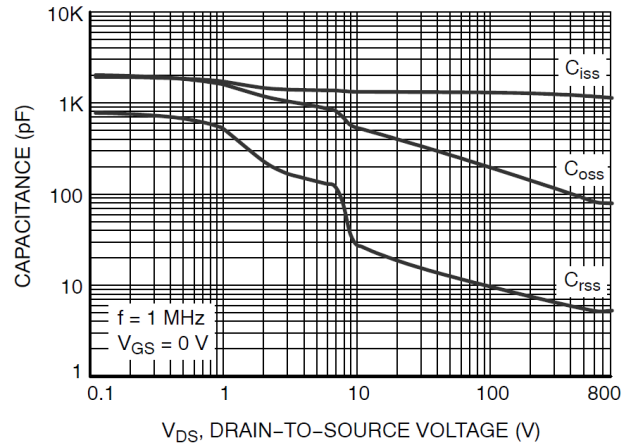


Figure 8. Capacitance vs. Drain-to-Source Voltage

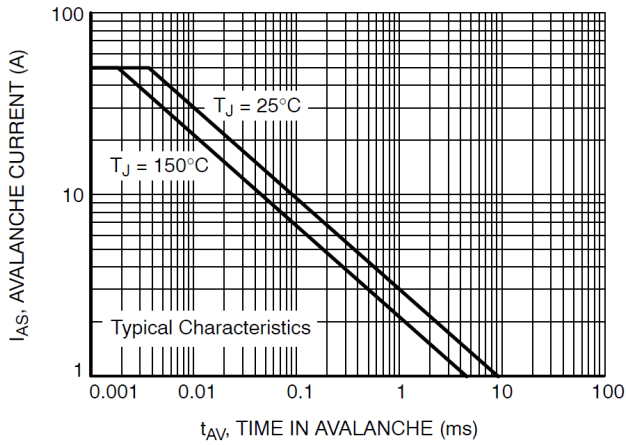


Figure 9. Unclamped Inductive Switching Capability

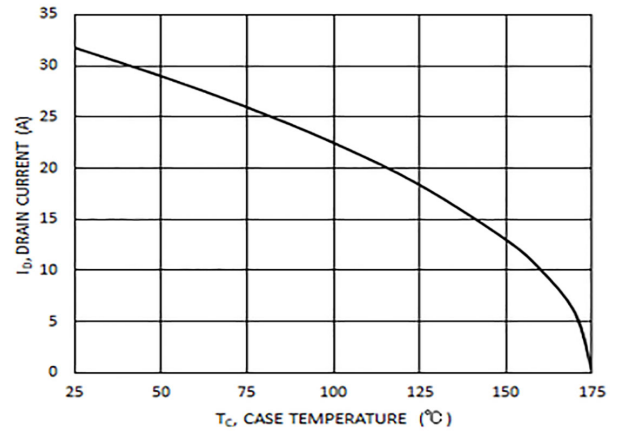


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

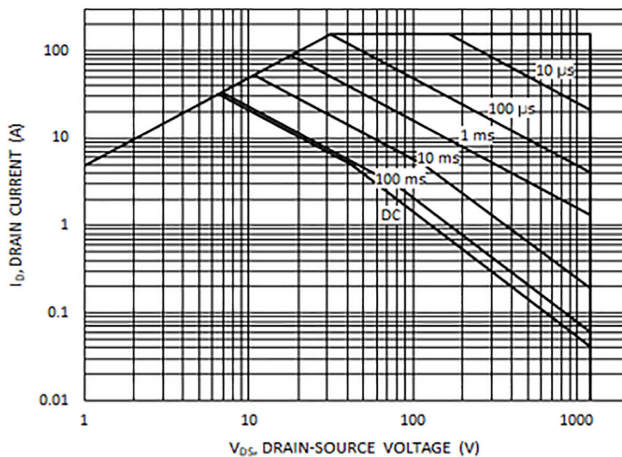


Figure 11. Safe Operating Area

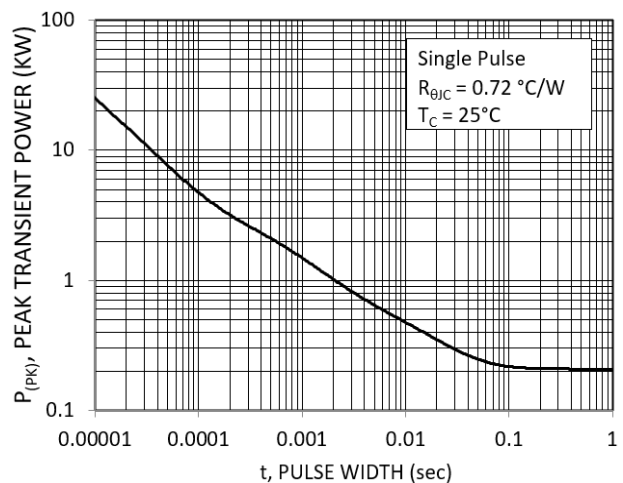


Figure 12. Single Pulse Maximum Power Dissipation

NVXK2PR80WXT2

TYPICAL CHARACTERISTICS (continued)

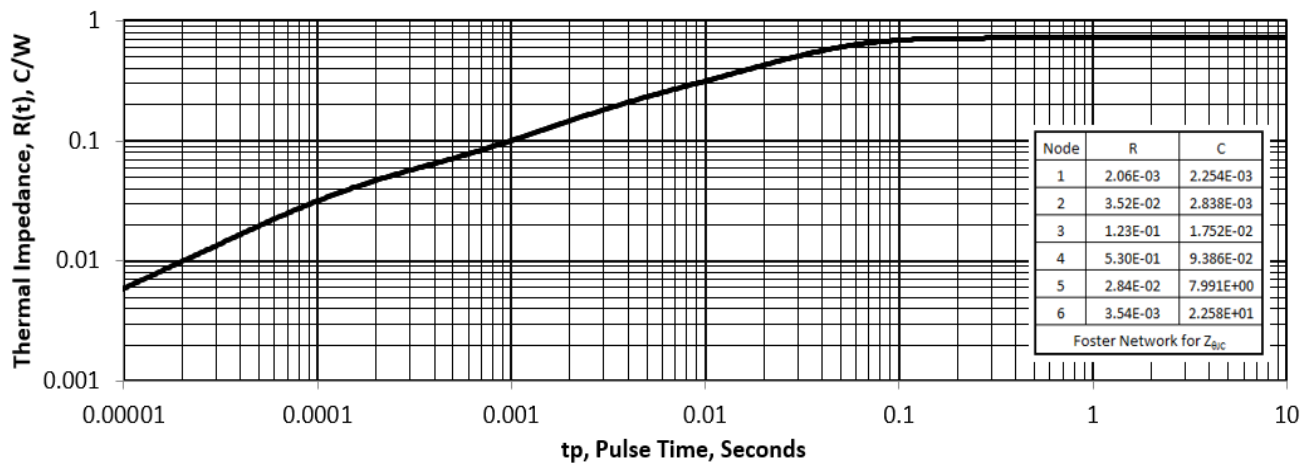
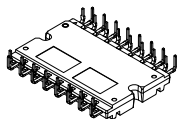
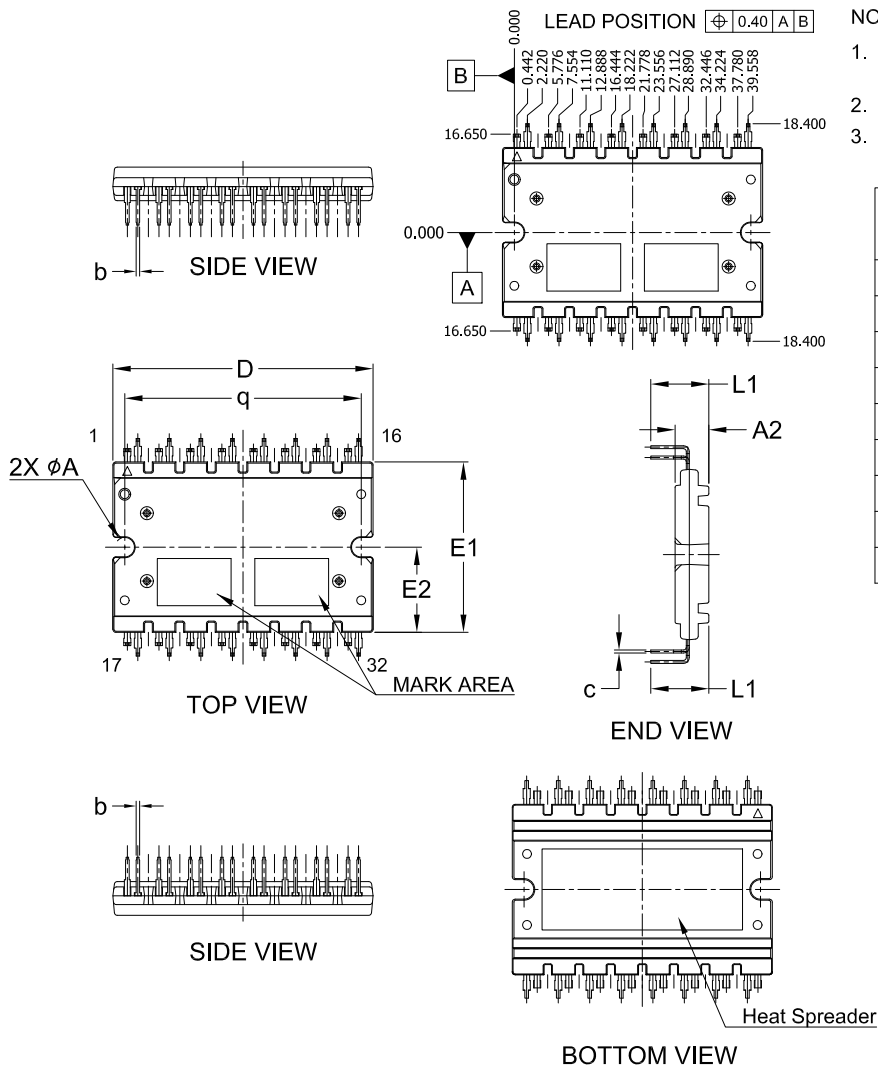


Figure 13. Thermal Response



APM32 44.00x28.80x5.70
CASE MODHM
ISSUE A

DATE 01 AUG 2023



NOTES:

1. DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A2	5.60	5.70	5.80
b	0.50	0.60	0.70
c	0.45	0.50	0.60
D	43.80	44.00	44.20
E1	28.60	28.80	29.00
E2	14.25	14.40	14.55
L1	9.50	9.80	10.10
q	39.85	40.00	40.15
ØA	3.20	3.30	3.40

GENERIC
MARKING DIAGRAM*

XXXXXXXXXXXXXXXXXX
ZZZ ATYWW
NNNNNNN

XXXX = Specific Device Code
ZZZ = Lot ID
AT = Assembly & Test Location
Y = Year
W = Work Week
NNN = Serial Number

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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